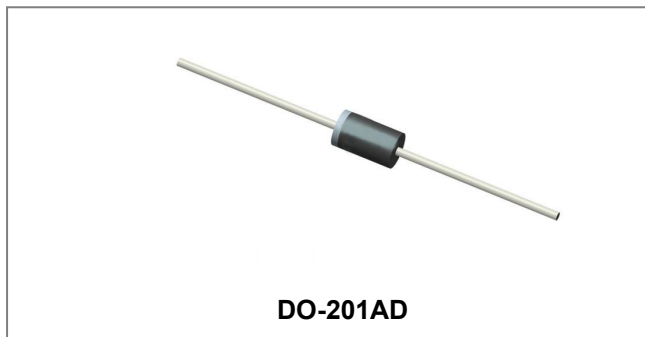


SB5200 SCHOTTKY RECTIFIER



Features

- Schottky Barrier Chip
- Guard Ring Die Construction for Transient Protection
- High Current Capability
- Low Power Loss, High Efficiency
- High Surge Current Capability
- For Use in Low Voltage, High Frequency Inverters, Free Wheeling, and Polarity Protection Applications
- This is a Pb – Free Device
- All SMC parts are traceable to the wafer lot
- Additional testing can be offered upon request

Circuit Diagram



Applications

- Switching power supply
- Converters
- Free-Wheeling diodes
- Reverse battery protection
- Disk drives
- Battery charging

Maximum Ratings:

Characteristics	Symbol	Condition	Max.	Units
Peak Repetitive Reverse Voltage Working Peak Reverse Voltage DC Blocking Voltage	V_{RRM} V_{RWM} V_R	-	200	V
Average Rectified Forward Current	$I_F (AV)$	50% duty cycle @ $T_A = 105^\circ\text{C}$, rectangular wave form	5	A
Peak One Cycle Non-Repetitive Surge Current	I_{FSM}	8.3 ms, half Sine pulse, $T_C = 25^\circ\text{C}$	120	A

Electrical Characteristics:

Characteristics	Symbol	Condition	Typ.	Max.	Units
Forward Voltage Drop*	V_{F1}	@ 5A, Pulse, $T_J = 25^\circ\text{C}$	0.85	1.10	V
	V_{F2}	@ 5A, Pulse, $T_J = 125^\circ\text{C}$	0.74	0.90	V
Reverse Current*	I_{R1}	@ $V_R = \text{Rated } V_R$, Pulse, $T_J = 25^\circ\text{C}$	0.0002	1	mA
	I_{R2}	@ $V_R = \text{Rated } V_R$, Pulse, $T_J = 125^\circ\text{C}$	0.05	7.0	mA
Junction Capacitance	C_T	@ $V_R = 5\text{V}$, $T_C = 25^\circ\text{C}$ $f_{SIG} = 1\text{MHz}$	150	200	pF
Series Inductance	L_S	Measured lead to lead 5 mm from package body	8.0	-	nH
Voltage Rate of Change	dv/dt	-	-	10,000	V/ μs

* Pulse width < 300 μs , duty cycle < 2%

Thermal-Mechanical Specifications:

Characteristics	Symbol	Condition	Specification	Units
Junction Temperature	T_J	-	-55 to +150	°C
Storage Temperature	T_{stg}	-	-55 to +150	°C
Typical Thermal Resistance Junction to Ambient	$R_{\theta JA}$	DC operation	10	°C/W
Approximate Weight	wt	-	1.02	g

Ratings and Characteristics Curves

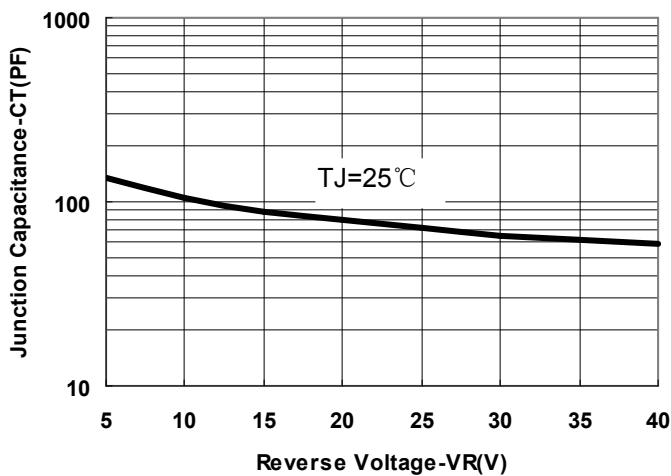


Fig.1-Typical Junction Capacitance

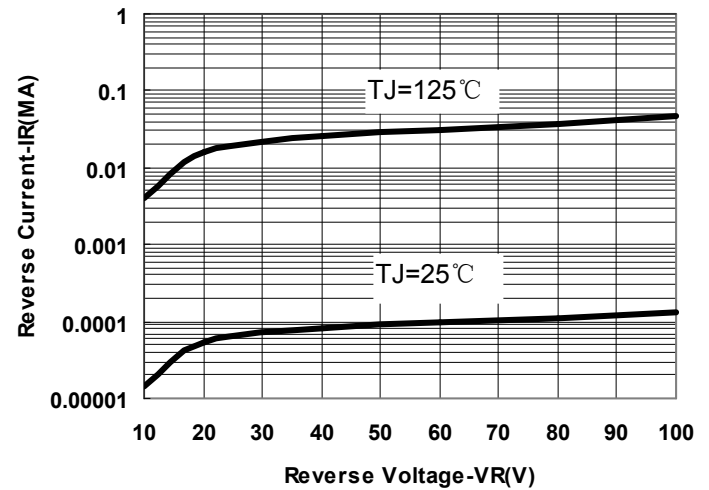


Fig.2-Typical Reverse Characteristics

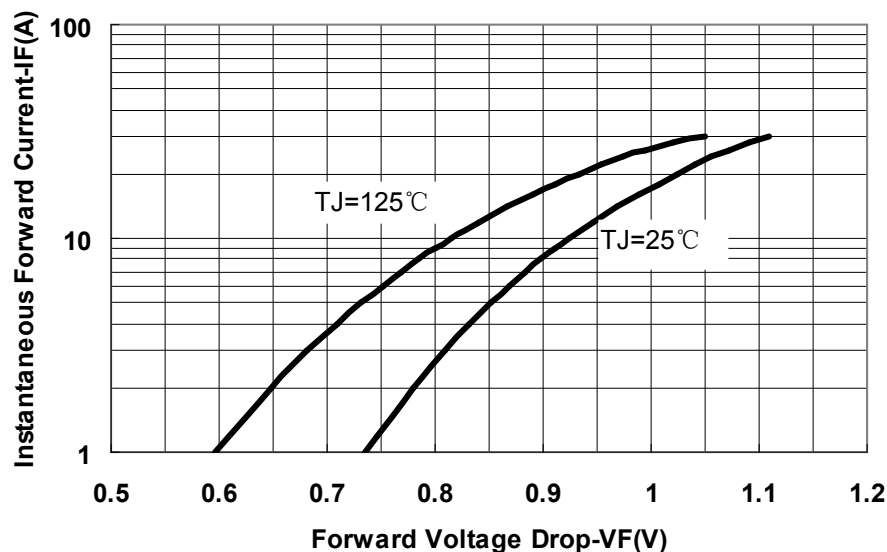
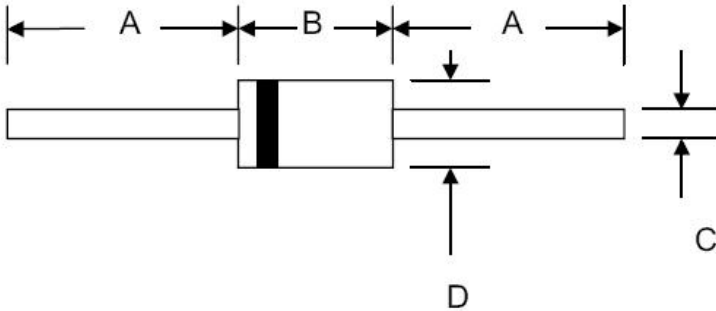


Fig.3-Typical Instantaneous Forward Voltage Characteristics

Mechanical Dimensions DO-201AD



SYMBOL	Millimeters		Inches	
	Min.	Max.	Min.	Max.
A	25.4	-	1.000	-
B	8.50	9.50	0.335	0.374
C	1.2	1.3	0.048	0.052
D	5.0	5.6	0.197	0.220

Ordering Information

Device	Package	Shipping
SB5200	DO-201AD (Pb-Free)	1250pcs / tape

For information on tape and reel specifications, including part orientation and tape sizes, please refer to our tape and reel packaging specification.

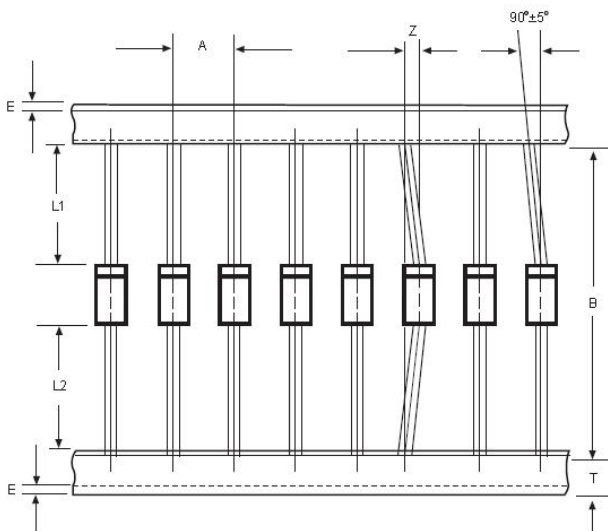
Marking Diagram



Where XXXXX is YYWWL

SB5200 = Part Name
SSG = SSG
YY = Year
WW = Week
L = Lot Number

Carrier Tape Specification DO-201AD



SYMBOL	Millimeters	
	Min.	Max.
A	9.50	10.50
B	50.9	53.9
Z	-	1.20
T	5.60	6.40
E	-	0.80
IL1-L2I	-	1.0

Technical Data
Data Sheet N0094, Rev. A



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